

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	33558	(@AD<"19970121") and ((air near gap) or void or (key adj hole)) and (substrate or board or chip or die or semiconductor or silicon)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:49
L2	4802	L1 and ((metallization or pattern or damascene or conductor or conductors or trace or traces or pattern) with (substrate or board or chip or die or semiconductor or silicon))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:50
L3	6600	L1 and ((metallization or pattern or damascene or conductor or conductors or trace or traces or pattern or line) with (substrate or board or chip or die or semiconductor or silicon))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:13
L4	2165	L2 and (semiconductor or "ic")	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:13
L5	76	438/For.224.ccls. and (@AD<"19970121")	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:22
L6	193	438/421.ccls. and (@AD<"19970121")	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:42
L7	75	L5 not L6	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:42
L8	29368	(@AD<"19970121") and ((air near gap) or void or (key adj hole)) and (substrate or chip or die or semiconductor or silicon)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:20
L9	13912	L8 and (metallization or pattern or wiring or damascene or conductor or conductors or trace or traces or pattern)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:22

L10	9145	L9 and (dielectric or insulation or insulating or oxide or sio or dioxide)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:22
L11	1101	L10 and (shield or crosstalk)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:52
L12	9145	L10 not L7	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:53
L13	1101	L11 not L7	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:53
L14	1100	L13 not L6	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:54
L15	888	L14 and air	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 12:54
L16	2	("5324683"   "5407860").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/17 13:10
L17	29368	(@AD<"19970121") and ((air near gap) or void or "air-gap" or (key adj hole)) and (substrate or chip or die or semiconductor or silicon)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:21
L18	494	L17 and (((air near gap) or void or "air-gap" or (key adj hole)) near (large or robust or big))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:42
L19	263	L18 and (metallization or pattern or wiring or damascene or conductor or conductors or trace or traces or pattern)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:22

L20	178	L19 and (dielectric or insulation or insulating or oxide or sio or dioxide)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:43
L21	135	L20 not L14	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:23
L22	583	L17 and (((air near gap) or void or "air-gap" or (key adj hole)) near (tall or height or wide or large or robust or big))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:27
L23	89	L22 not L18	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:30
L24	1	("5641712").PN.	USPAT	OR	OFF	2005/03/17 13:30
L25	1	("5759913").PN.	USPAT	OR	OFF	2005/03/17 13:30
L26	2	("5324683"   "5407860").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/17 13:33
L27	32	("5759913").URPN.	USPAT	OR	OFF	2005/03/17 13:33
L28	21	("3689992"   "5310700"   "5324683"   "5407860"   "5444015"   "5461003"   "5510645"   "5641712"   "5750415"   "5759913"   "5814555"   "5837618"   "5924006"   "5932490"   "5949143"   "6025260"   "6054381"   "6071805"   "6077767"   "6093633"   "6130151").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/17 13:35
L29	1	L17 and (((air near gap) or void or "air-gap" or (key adj hole)) near (float or floating))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:39
L30	1	("6165890").PN.	USPAT	OR	OFF	2005/03/17 13:39
L31	595	L17 and (((air near gap) or void or "air-gap" or (key adj hole)) near size)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:46

L32	0	L31 and (crosstalk with size)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:43
L33	558	L31 not L22	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:43
L34	371	L33 and (dielectric or insulation or insulating or oxide or sio or dioxide)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:46
L35	186	L17 and (((air near gap) or void or "air-gap" or (key adj hole)) near (under or underneath or below))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:46
L36	120	L35 and (dielectric or insulation or insulating or oxide or sio or dioxide)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/17 13:46